Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A stent comprising a compound including Ti, N, C, or including Ti, N, O, or both, implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent and a layer of TiN_xC_y disposed over the compound.

2. (Previously Presented) The stent of Claim 21, wherein x is 1 and y is 1 or 2.

3. (Currently amended) The stent of Claim 21, wherein the depth of ~~the~~ an implanted TiN_xO_y compound is not greater than about 2000 Å from the surface of the stent.

4. (Currently Amended) The stent of Claim 21, wherein the layer ~~additionally comprising a layer~~ of TiN_xO_y is exposed on the surface of the stent ~~compound deposited on the region of the surface of the stent where the TiN_xO_y compound is implanted~~.

5. (Original) The stent of Claim 4, wherein x is 1 and y is 1 or 2.

6. (Original) The stent of Claim 4, wherein the layer of TiN_xO_y compound is not more than about 48,000 Å in thickness.

7. (Original) The stent of Claim 1, wherein the stent is made from stainless steel.

8. (Original) The stent of Claim 1, wherein the surface is the tissue-contacting surface of the stent.

9. (Currently Amended) A stent comprising a layer of ~~TiN_xO_y or~~ TiN_xC_y on a surface of the stent and a subsurface compound including Ti, N, or TiN disposed beneath the layer of ~~TiN_xO_y or~~ TiN_xC_y, wherein the subsurface compound is intermixed with a surface material of the stent.

10. (Currently Amended) The stent of Claim 9, wherein a region of the layer of ~~TiN_xO_y or~~ TiN_xC_y is implanted at a depth within a surface of the stent.

11. (Canceled).

12. (Canceled).

13. (Currently Amended) A method of modifying a surface of a stent, comprising implanting a compound including Ti, N, C, or including Ti, N, O, or both, on a molecular or atomic level at a depth within a surface of the stent, followed by depositing TiN_xC_y over the implanted compound.

14. (Currently amended) The method of Claim ~~22~~ 13, wherein x is 1 and y is 1 or 2.

15. (Canceled).

16. (Canceled).

17. (Original) The method of Claim 13, wherein the stent is made from stainless

steel.

18. (Previously Presented) The method of Claim 13, wherein prior to the act of implanting the compound including Ti, N, C, or including Ti, N, O, or both, within the surface of the stent, the method comprises implanting Ti, N or TiN within the surface of the stent.

19. (Currently Amended) A method of modifying a stent surface, comprising implanting Ti [[,]] or N~~, or TiN~~ into the surface of the stent on a molecular or atomic level, followed by implanting TiN over the Ti or N, and followed by ~~and~~ forming a layer of a TiN_xO_y ~~or TiN_xC_y~~ compound over at least some of the areas where ~~Ti, N, or~~ TiN has been implanted.

20. (Canceled).

21. (Previously Presented) A stent comprising a first region having Ti or N implanted on a molecular or atomic level at a depth with at least a region of a surface of the stent, a second region over the first region having TiN implanted on a molecular or atomic level at a depth with at least a region of a surface of the stent and a layer of TiN_xO_y compound over the second region ~~implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent~~.

22. (Canceled).

23. (Canceled).

24. (Currently Amended) The stent of Claim ~~23~~ 21, wherein the stent is made from stainless steel.

25. (Currently Amended) The stent of Claim ~~23~~ 21, wherein the surface is the tissue-contacting surface of the stent.

26. (Currently Amended) A stent comprising a layer of ~~TiN_xO_y or~~ TiN_xC_y exposed on the surface of the stent, the stent having a surface material different than ~~TiN_xO_y or~~ TiN_xC_y and a compound including Ti, N, or TiN, disposed beneath the layer of ~~TiN_xO_y or~~ TiN_xC_y such that the compound is blended with the surface material of the stent.

27. (Currently Amended) The stent of Claim 26, wherein a region of the layer of ~~TiN_xO_y or~~ TiN_xC_y is implanted at a depth within a surface of the stent.

28. (Canceled).

29. (Canceled).

30. (Canceled).

31. (Canceled).

32. (Canceled).

33. (Canceled).

34. (Previously Presented) A stent comprising a TiN_xC_y compound implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent.

35. (Canceled).

36. (Canceled).

37. (Canceled).

38. (Canceled).

39. (Canceled).

40. (Canceled).

41. (Canceled).

42. (Previously Presented) The stent of Claim 34, additionally comprising a layer of a TiN_xC_y compound on the region of the surface of the stent wherein the TiN_xC_y compound is implanted.

43. (Currently Amended) A method of modifying a stent surface, comprising implanting ~~by plasma reaction~~ on a molecular or atomic level Ti, N, or TiN into the surface of the stent and forming a layer of a ~~TiN_xO_y~~ TiN_xC_y compound over the areas where Ti, N, or TiN has been implanted.

44. (Previously Presented) A method of modifying a surface of a stent, comprising implanting a TiN_xC_y compound on a molecular or atomic level at a depth within a surface of the stent or depositing the compound on the surface of the stent.

45. (Currently Amended) The stent of Claim 1, wherein the layer of ~~additionally comprising a layer of TiN_xO_y or~~ TiN_xC_y is exposed on a surface of the stent.